

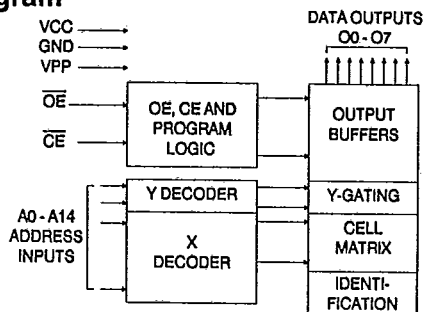
AT27C256

T-46-13-29

Features

- Low Power CMOS Operation
 - 100 μ A max. Standby
 - 30 mA max. Active at 5 MHz
- Fast Read Access Time - 120ns
- Wide Selection of JEDEC Standard Packages including OTP
 - 28-Lead 600 mil Cerdip and OTP Plastic DIP or SOIC
 - 32-Pad LCC and OTP PLCC
- 5V $\pm$ 10% Supply
- High Reliability Latch-Up Resistant CMOS Technology
 - 2000V ESD Protection
- Fast Programming - 4ms/byte (typical)
- Two-line Control
- CMOS and TTL Compatible Inputs and Outputs
- Integrated Product Identification Code
- Full Military, Commercial and Industrial Temperature Ranges

Block Diagram



Description

The AT27C256 is a low-power, high performance 262,144 bit Ultraviolet Erasable and Electrically Programmable Read Only Memory (EPROM) organized 32K x 8. It requires only one 5V power supply in normal read mode operation. Any byte can be accessed in less than 120ns, making this part compatible with high performance microprocessor systems by eliminating the need for speed-reducing WAIT states.

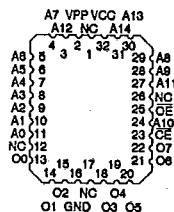
Atmel's 1.5-micron CMOS technology provides optimum speed, low-power and high noise immunity. Power consumption is typically only 10mA in Active Mode and less than 1 μ A in Standby. Atmel's CMOS EPROM process uses industry-proven floating poly EPROM technology to provide high quality and manufacturability.

The AT27C256 comes in a choice of industry standard JEDEC-approved packages including; 28-pin DIP in ceramic or one time programmable (OTP) plastic, 28-pin OTP plastic small outline (SOIC), and 32-pad ceramic leadless chip carrier (LCC) or OTP plastic J-leaded chip carrier (PLCC). The device features two-line control ($\overline{CE}$, $\overline{OE}$) to give designers the flexibility to prevent bus contention.

Pin Configurations

Pin Name	Function
A0-A14	Addresses
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
NC	No Connect
Q0-Q7	Outputs

VPP	1	28	VCC
A12	2	27	A14
A7	3	26	A13
A6	4	25	A2
A5	5	24	A9
A4	6	23	A11
A3	7	22	A10
A2	8	21	A1
A1	9	20	CE
A0	10	19	Q7
Q0	11	18	Q6
Q1	12	17	Q5
Q2	13	16	Q4
GND	14	15	Q3



Note: PLCC Package Pins 1 and 17 are DON'T CONNECT.



256K (32K x 8)

UV

Erasable

CMOS

EPROM

4



Description (Continued)

With a high density 32K byte storage capability, Atmel's 27C256 allows firmware to be stored reliably and to be quickly accessed by the system without the delays of mass storage media.

The AT27C256 has additional features to ensure high quality and efficient production use. The fast programming algorithm reduces the time required to program the chip and guarantees reliable programming. The Integrated Product Identification Code electronically identifies the device and manufacturing origin. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages.

Erasure Characteristics

The entire memory array of the AT27C256 is erased (all outputs read as V_{OH}) after exposure to ultraviolet light at a wavelength of 2537Å. Complete erasure is assured after a minimum of 20 minutes exposure using $12,000 \mu W/cm^2$ intensity lamps spaced one inch away from the chip. Minimum erase time for lamps at other intensity ratings can be calculated from the minimum integrated erasure dose of $15W \cdot sec/cm^2$. To prevent unintentional erasure, an opaque label is recommended to cover the clear window on any UV erasable EPROM which will be subjected to continuous fluorescent indoor lighting or sunlight.

Absolute Maximum Ratings*

Temperature Under Bias	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on Any Pin with Respect to Ground	-2.0V to +7.0V ⁽¹⁾
Voltage on A9 with Respect to Ground	-2.0V to +14.0V ⁽¹⁾
V _{PP} Supply Voltage with Respect to Ground	-2.0V to +14.0V ⁽¹⁾
Integrated UV Erase Dose.....	7258 w·sec/cm ²

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Notes:

1. Minimum voltage is -0.6V dc which may undershoot to -2.0V for pulses of less than 20ns. Maximum output pin voltage is $V_{CC}+0.75V$ dc which may overshoot to +7.0V for pulses of less than 20ns.

Operating Modes

MODE \ PIN	$\overline{CE}$	$\overline{OE}$	Ai	V _{PP}	V _{CC}	Outputs
Read	V _{IL}	V _{IL}	Ai	V _{CC}	V _{CC}	DOUT
Output Disable	V _{IL}	V _{IH}	X ⁽¹⁾	V _{CC}	V _{CC}	High Z
Standby	V _{IH}	X	X	V _{CC}	V _{CC}	High Z
Fast Program ⁽²⁾	V _{IL}	V _{IH}	Ai	V _{PP}	V _{CC}	DIN
PGM Verify ⁽²⁾	X	V _{IL}	Ai	V _{PP}	V _{CC}	DOUT
Optional PGM Verify ⁽²⁾	V _{IL}	V _{IL}	Ai	V _{CC}	V _{CC}	DOUT
PGM Inhibit ⁽²⁾	V _{IH}	V _{IH}	X	V _{PP}	V _{CC}	High Z
Product Identification ⁽⁴⁾	V _{IL}	V _{IL}	A9 = V _{IH} ⁽³⁾ A0 = V _{IH} or V _{IL} A1-A14 = V _{IL}	V _{CC}	V _{CC}	Identification Code

Notes: 1. X can be V_{IL} or V_{IH}.

2. Refer to Programming characteristics.

3. V_{IH} = $12.0 \pm 0.5V$.

4. Two identifier bytes may be selected. All Ai inputs are held low (V_{IL}), except A9 which is set to V_{IH} and A0 which is toggled low (V_{IL}) to select the Manufacturer's Identification byte and high (V_{IH}) to select the Device Code byte.

AT27C256

T-46-13-29

D.C. and A.C. Operating Conditions for Read Operation

AT27C256						
		-12	-15	-17	-20	-25
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
	Mil.		-55°C - 125°C	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C
Vcc Power Supply		5V ± 10%	5V ± 10%	5V ± 10%	5V ± 10%	5V ± 10%

D.C. and Operating Characteristics for Read Operation

Symbol	Parameter	Condition	Min	Max	Units
I _{LI}	Input Load Current	V _{IN} = -0.1V to V _{CC} + 1V		10	μA
I _{LO}	Output Leakage Current	V _{OUT} = -0.1V to V _{CC} + 0.1V		10	μA
I _{PP1} (2)	V _{PP} (1) Read/Standby Current	V _{PP} = 3.8 to V _{CC} + 0.3V		10	μA
I _{SB}	V _{CC} (1) Standby Current	I _{SB1} (CMOS)	Com.	100	μA
		CE = V _{CC} - 0.3 to V _{CC} + 1.0V	Ind., Mil.	200	μA
		I _{SB2} (TTL)	Com.	2	mA
		CE = 2.0 to V _{CC} + 1.0V	Ind., Mil.	3	mA
I _{CC}	V _{CC} Active Current	f = 5MHz, I _{OUT} = 0mA, CE = V _{IL}	Com.	30	mA
			Ind., Mil.	40	mA
V _{IL}	Input Low Voltage		-0.6	0.8	V
V _{IH}	Input High Voltage		2.0	V _{CC} + 1	V
V _{OL}	Output Low Voltage	I _{OL} = 2.1mA		.45	V
V _{OH}	Output High Voltage	I _{OH} = -100μA		V _{CC} - 0.3	V
		I _{OH} = -2.5mA		3.5	V
		I _{OH} = -400μA		2.4	V
V _{PP}	V _{PP} Read Voltage	V _{CC} = 5 ± 0.5V	3.8	V _{CC} + .3	V

Notes: 1. V_{CC} must be applied simultaneously or before V_{PP}, and removed simultaneously or after V_{PP}.

2. V_{PP} may be connected directly to V_{CC}, except during programming. The supply current would then be the sum of I_{CC} and I_{PP}.

A.C. Characteristics for Read Operation

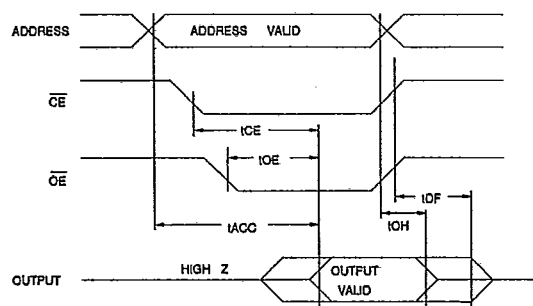
			AT27C256										Units
			-12		-15		-17		-20		-25		
Symbol	Parameter	Condition	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t _{ACC} (4)	Address to Output Delay	$\overline{CE} = \overline{OE}$ = V _{IL}	120		150		170		200		250		ns
		Com., Ind. Mil.			150		170		200		250		ns
t _{CE} (3)	$\overline{CE}$ to Output Delay	$\overline{OE} = V_{IL}$	120		150		170		200		250		ns
t _{OE} (3,4)	$\overline{OE}$ to Output Delay	$\overline{CE} = V_{IL}$	60		70		70		75		100		ns
t _{DF} (2,5)	$\overline{OE}$ or $\overline{CE}$ High to Output Float	$\overline{CE} = V_{IL}$	45		50		50		55		60		ns
t _{OH}	Output Hold from Address, $\overline{CE}$ or $\overline{OE}$, whichever occurred first	$\overline{CE} = \overline{OE}$ = V _{IL}	0		0		0		0		0		ns

Notes: 2, 3, 4, 5. - see AC Waveforms for Read Operation.





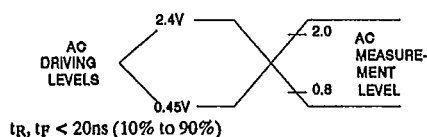
A.C. Waveforms for Read Operation ⁽¹⁾



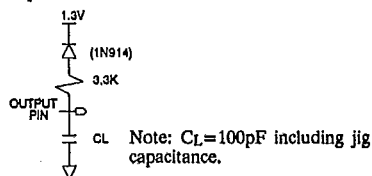
Notes:

1. Timing measurement references are 0.8V and 2.0V. Input AC driving levels are 0.45V and 2.4V, unless otherwise specified.
2. t_{DF} is specified from $\overline{OE}$ or $\overline{CE}$, whichever occurs first. Output float is defined as the point when data is no longer driven.
3. $\overline{OE}$ may be delayed up to t_{CE-tOE} after the falling edge of $\overline{CE}$ without impact on t_{CE} .
4. $\overline{OE}$ may be delayed up to $t_{ACC-tOE}$ after the address is valid without impact on t_{ACC} .
5. This parameter is only sampled and is not 100% tested.

Input Test Waveforms and Measurement Levels



Output Test Load

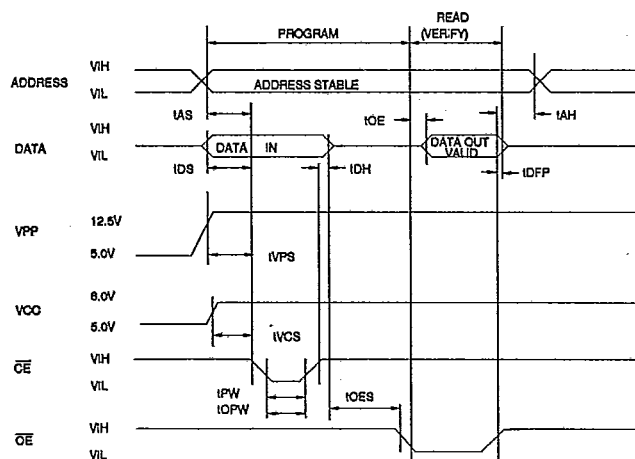


Pin Capacitance ($f=1\text{MHz}$ $T=25^\circ\text{C}$) ⁽¹⁾

	Typ	Max	Units	Conditions
C_{IN}	4	6	pF	$V_{IN} = 0V$
C_{OUT}	8	12	pF	$V_{OUT} = 0V$

Notes: 1. Typical values for nominal supply voltage. This parameter is only sampled and is not 100% tested.

Programming Waveforms ⁽¹⁾



Notes:

1. The Input Timing Reference is 0.8V for V_{IL} and 2.0V for V_{IH} .
2. t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.
3. When programming the AT27C256 a $0.1\mu\text{F}$ capacitor is required across V_{PP} and ground to suppress spurious voltage transients.

D.C. Programming Characteristics
 $T_A = 25 \pm 5^\circ\text{C}$, $V_{CC} = 6.0 \pm 0.25\text{V}$, $V_{PP} = 12.5 \pm 0.5\text{V}$

Sym- bol	Parameter	Test Conditions	Limits		Units
			Min	Max	
I_{IL}	Input Load Current	$V_{IN} = V_{IL}, V_{IH}$		10	μA
V_{IL}	Input Low Level	(All Inputs)	-0.6	0.8	V
V_{IH}	Input High Level		2.0	$V_{CC} + 1$	V
V_{OL}	Output Low Volt.	$I_{OL} = 2.1\text{mA}$		.45	V
V_{OH}	Output High Volt.	$I_{OH} = -400\mu\text{A}$	2.4		V
I_{CC2}	V_{CC} Supply Current (Program and Verify)			30	mA
I_{PP2}	V_{PP} Supply Current	$\overline{CE} = V_{IL}$		25	mA
V_{ID}	A9 Product Iden- tification Voltage		11.5	12.5	V

A.C. Programming Characteristics
 $T_A = 25 \pm 5^\circ\text{C}$, $V_{CC} = 6.0 \pm 0.25\text{V}$, $V_{PP} = 12.5 \pm 0.5\text{V}$

Sym- bol	Parameter	Test Conditions* (see Note 1)	Limits		Units
			Min	Max	
t_{AS}	Address Setup Time		2		μs
t_{OES}	$\overline{OE}$ Setup Time		2		μs
t_{DS}	Data Setup Time		2		μs
t_{AH}	Address Hold Time		0		μs
t_{DH}	Data Hold Time		2		μs
t_{DFP}	$\overline{OE}$ High to Out- put Float Delay	(Note 2)	0	130	ns
t_{VPS}	V_{PP} Setup Time		2		μs
t_{VCS}	V_{CC} Setup Time		2		μs
t_{PW}	$\overline{CE}$ Initial Pro- gram Pulse Width	(Note 3)	0.95	1.05	ms
t_{OPW}	$\overline{CE}$ Overprogram Pulse Width	(Note 4)	2.85	78.75	ms
t_{OE}	Data Valid from $\overline{OE}$			150	ns

***A.C. Conditions of Test:**

Input Rise and Fall Times (10% to 90%) 20ns
 Input Pulse Levels 0.45V to 2.4V
 Input Timing Reference Level 0.8V to 2.0V
 Output Timing Reference Level 0.8V to 2.0V

Notes:

- V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP} .
- This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram.
- Initial Program Pulse width tolerance is $1\text{msec} \pm 5\%$.
- The length of the overprogram pulse may vary from 2.85 msec to 78.75 msec as a function of the iteration counter value X.

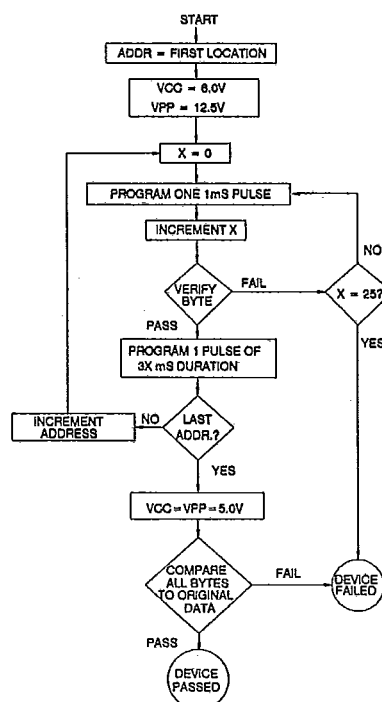
**Atmel's 27C256 Integrated
Product Identification Code:**

Codes	Pins									Hex Data
	A0	O7	O6	O5	O4	O3	O2	O1	O0	
Manufacturer	0	0	0	1	0	1	0	0	1	29
Device Type	1	1	0	0	0	1	1	0	0	8C

Fast Programming Algorithm

Two $\overline{CE}$ pulse widths are used to program; initial and over-program. A_i are set to address the desired byte. V_{CC} is raised to 6.0V. The first $\overline{CE}$ pulse is 1ms. The programmed byte is then verified. If the byte programmed successfully, then an overprogram $\overline{CE}$ pulse is applied for 3ms. If the byte fails to program after the first 1ms pulse, then up to 25 successive 1ms pulses are applied with a verification after each pulse. When the byte passes verification, the overprogram pulse width is 3X (times) the number of 1ms pulses required earlier (75ms max).

If the part fails to verify after 25 1ms pulses have been applied, it is considered as failed. After the first byte is programmed, the A_i are set to the next address repeating the algorithm until all required addresses are programmed. Then V_{CC} is lowered to 5.0V. All bytes subsequently are read to compare with the original data to determine if the device passes or fails.





Ordering Information

ATMEL CORP

29E D

t _{ACC} (ns)	I _{CC} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
120	30	0.1	AT27C256-12DC AT27C256-12LC	28DW6 32LW	Commercial (0°C to 70°C)
120	40	0.2	AT27C256-12DI AT27C256-12LI	28DW6 32LW	Industrial (-40°C to 85°C)
150	30	0.1	AT27C256-15DC AT27C256-15LC AT27C256-15PC AT27C256-15JC AT27C256-15RC	28DW6 32LW 28P6 32J 28R	Commercial (0°C to 70°C)
150	40	0.2	AT27C256-15DI AT27C256-15LI AT27C256-15PI AT27C256-15JI AT27C256-15RI	28DW6 32LW 28P6 32J 28R	Industrial (-40°C to 85°C)
			AT27C256-15DM AT27C256-15LM	28DW6 32LW	Military (-55°C to 125°C)
			AT27C256-15DM/883 AT27C256-15LM/883	28DW6 32LW	Military/883C Class B, Fully Compliant (-55°C to 125°C)
170	30	0.1	AT27C256-17DC AT27C256-17LC AT27C256-17PC AT27C256-17JC AT27C256-17RC	28DW6 32LW 28P6 32J 28R	Commercial (0°C to 70°C)
170	40	0.2	AT27C256-17DI AT27C256-17LI AT27C256-17PI AT27C256-17JI AT27C256-17RI	28DW6 32LW 28P6 32J 28R	Industrial (-40°C to 85°C)
			AT27C256-17DM AT27C256-17LM	28DW6 32LW	Military (-55°C to 125°C)
			AT27C256-17DM/883 AT27C256-17LM/883	28DW6 32LW	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	30	0.1	AT27C256-20DC AT27C256-20LC AT27C256-20PC AT27C256-20JC AT27C256-20RC	28DW6 32LW 28P6 32J 28R	Commercial (0°C to 70°C)
200	40	0.2	AT27C256-20DI AT27C256-20LI AT27C256-20PI AT27C256-20JI AT27C256-20RI	28DW6 32LW 28P6 32J 28R	Industrial (-40°C to 85°C)

ATMEL CORP

T-46-13-29

Ordering Information

t _{ACC} (ns)	I _{CC} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
200	40	0.2	AT27C256-20DM AT27C256-20LM	28DW6 32LW	Military (-55°C to 125°C)
			AT27C256-20DM/883 AT27C256-20LM/883	28DW6 32LW	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	30	0.1	AT27C256-25DC AT27C256-25LC AT27C256-25PC AT27C256-25JC AT27C256-25RC	28DW6 32LW 28P6 32J 28R	Commercial (0°C to 70°C)
250	40	0.2	AT27C256-25DI AT27C256-25LI AT27C256-25PI AT27C256-25JI AT27C256-25RI	28DW6 32LW 28P6 32J 28R	Industrial (-40°C to 85°C)
			AT27C256-25DM AT27C256-25LM	28DW6 32LW	Military (-55°C to 125°C)
			AT27C256-25DM/883 AT27C256-25LM/883	28DW6 32LW	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300	40	0.2	AT27C256-30DM/883 AT27C256-30LM/883	28DW6 32LW	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350	40	0.2	AT27C256-35DM/883 AT27C256-35LM/883	28DW6 32LW	Military/883C Class B, Fully Compliant (-55°C to 125°C)

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Package Type

28DW6	28 Lead, 0.600" Wide, Windowed, Ceramic Dual Inline Package (Cerdip)
32J	32 Lead, Plastic J-Leaded Chip Carrier OTP (PLCC)
32LW	32 Pad, Windowed, Ceramic Leadless Chip Carrier (LCC)
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package OTP (PDIP)
28R	28 Lead, 0.330" Wide, Plastic Gull Wing Small Outline OTP (SOIC)

